







**SEMICONDUCTOR WAFER CLEANING AGENT AND CLEANING METHOD**

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 EP0897975  
 JP9255991  
 JP10026832  
 JP11040526  
more >>**Abstract of WO0171789**

A semiconductor surface cleaning agent containing a compound the molecule of which has a nitrogen atom having an unshared electron pair and used for cleaning the surface of a semiconductor on which copper wiring is provided, and a method for cleaning the surface of a semiconductor characterized by treating the surface of a semiconductor on which copper wiring is provided with such a cleaning agent. The cleaning agent does not corrode the copper wiring (copper thin film) on the semiconductor and SiO<sub>2</sub> of the interlayer insulating film, does not impair the flatness of the surface, and is effective in removing CuO and particles adhering to the surface at the Cu-CMP step.

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